

ABSTRACT:

A method of manufacturing an electronic device, a semiconductor device in particular but not exclusively, which method comprises the steps of:

- applying a semiconductor substrate (1) which is provided with a conductor (3,4,5) at a surface (2), the conductor (3,4,5) having a top surface portion (6) and sidewall portions (7),
5 of which at least the top surface portion (6) is provided with an etch stop layer (12) comprising silicon carbide,

- applying a dielectric layer (13),

- etching a via (14,15,16) in the dielectric layer (13) over the conductor (3,4,5), and stopping on the etch stop layer (12) to create an exposed part of the etch stop layer (12),

10 - removing the exposed part of the etch stop layer (12) inside the via (14,15,16) from at least the top surface portion (6) of the conductor (3,4,5),

- filling the via (14,15,16) with a conductive material (18).

15 Fig. 4